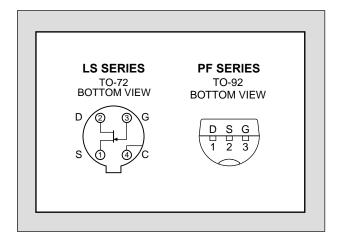


## Linear Integrated Systems

| FEATURES  |                          |  |  |  |
|---|--------------------------|--|--|--|
| DIRECT REPLACEMENT FOR LF5301, PF5301, & 2N5301 |                          |  |  |  |
| HIGH INPUT INPEDANCE                            | $I_G = 0.100 \text{ pA}$ |  |  |  |
| HIGH GAIN                                       | g <sub>fs</sub> = 70 μS  |  |  |  |
| ABSOLUTE MAXIMUM RATINGS <sup>1</sup>           |                          |  |  |  |
| @ 25 °C (unless otherwise stated)               |                          |  |  |  |
| Maximum Temperatures                            |                          |  |  |  |
| Storage Temperature (TO-72)                     | -65 to 175°C             |  |  |  |
| Storage Temperature (TO-92)                     | -65 to 150°C             |  |  |  |
| Maximum Power Dissipation                       |                          |  |  |  |
| Continuous Power Dissipation                    | 300mW                    |  |  |  |
| Maximum Currents                                |                          |  |  |  |
| Gate Current                                    | 50mA                     |  |  |  |
| Maximum Voltages                                |                          |  |  |  |
| Gate to Drain                                   | -30V                     |  |  |  |
| Gate to Source                                  | -30V                     |  |  |  |

# LS5301, PF5301

## **VERY HIGH INPUT IMPEDANCE N-CHANNEL JFET**



#### COMMON ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

| SYMBOL           | CHARACTERISTIC                     | MIN | TYP  | MAX | UNIT   | CONDITIONS                                     |
|------------------|------------------------------------|-----|------|-----|--------|--|
| $BV_GSS$         | Gate to Source Breakdown Voltage   | -30 |      |     | \<br>\ | $V_{DS} = 0V$ , $I_D = -1\mu A$                |
| $V_{GS(off)}$    | Gate to Source Cutoff Voltage      | 0.6 |      | 3.0 | V      | $V_{DS} = 10V, I_{D} = 1nA$                    |
| I <sub>GSS</sub> | Gate Leakage Current               |     |      | -1  | nΛ     | $V_{DS} = 0V$ , $V_{GS} = -15V$                |
| I <sub>G</sub>   | Gate Operating Current             |     | 0.04 |     | рA     | $V_{DG} = 6V, I_{D} = 5\mu A$                  |
| I <sub>DSS</sub> | Drain to Source Saturation Current | 30  |      | 500 | μA     | $V_{DS}$ = 10V, $V_{GS}$ = 0V                  |
| <b>g</b> fs      | Forward Transconductance           | 70  |      | 300 | μS     | $V_{DS} = 10V, V_{GS} = 0V, f = 1kHz$          |
| C <sub>iss</sub> | Input Capacitance                  |     |      | 3   | pF     | $V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$          |
| C <sub>rss</sub> | Reverse Transfer Capacitance       |     |      | 1.5 | ρr     | VDS - 10V, VGS - 0V, I - 11VII 12              |
| e <sub>n</sub>   | Equivalent Noise Voltage           |     | 45   | 150 | nV/√Hz | $V_{DG} = 10V$ , $I_D = 50\mu A$ , $f = 100Hz$ |

### **NOTES**

Absolute maximum ratings are limiting values above which serviceability may be impaired.

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